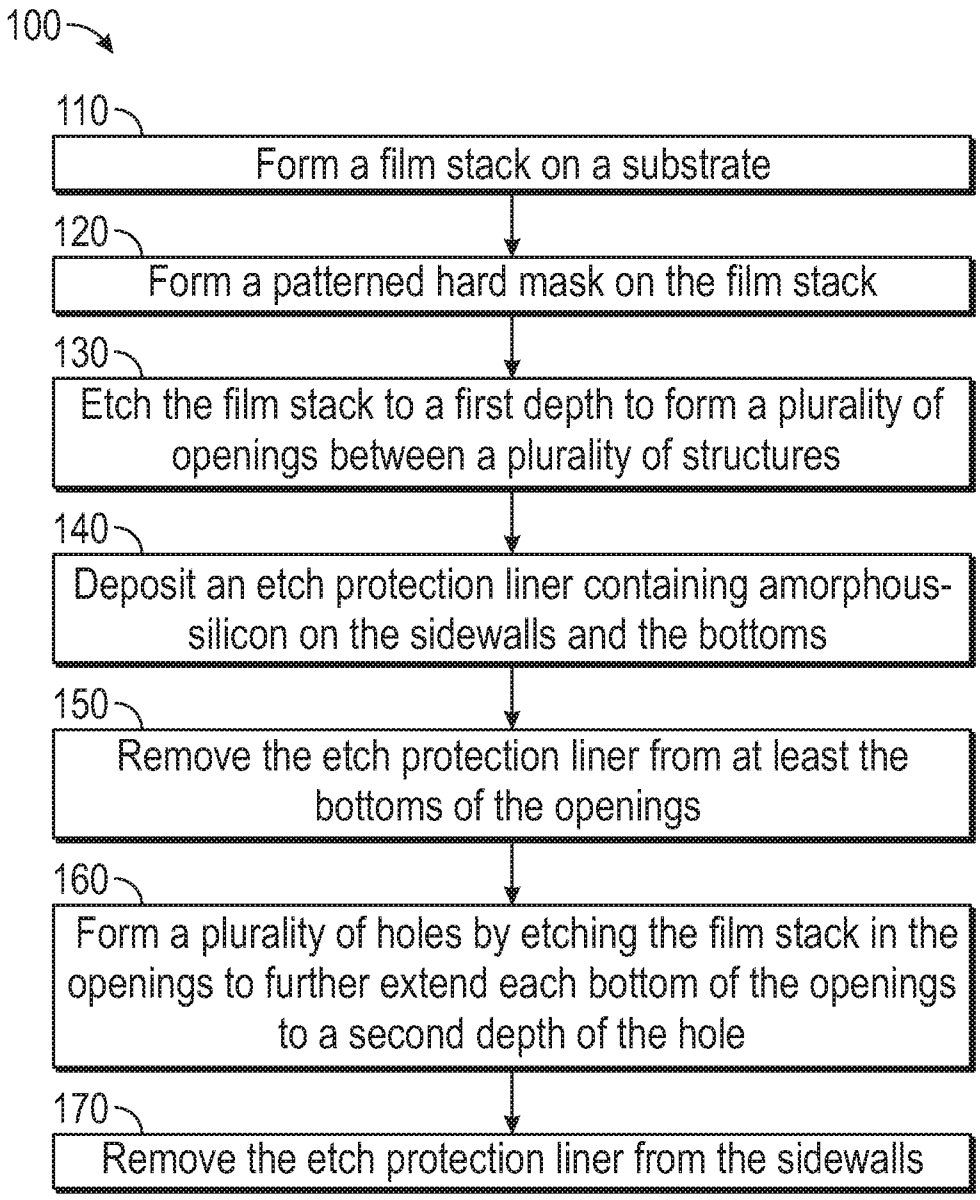

100
110
Form a film stack on a substrate
120
Form a patterned hard mask on the film stack
130
Etch the film stack to a first depth to form a plurality of openings between a plurality of structures
140
Deposit an etch protection liner containing amorphous-silicon on the sidewalls and the bottoms
150
Remove the etch protection liner from at least the bottoms of the openings
160
Form a plurality of holes by etching the film stack in the openings to further extend each bottom of the openings to a second depth of the hole
170
Remove the etch protection liner from the sidewalls

FIG. 1

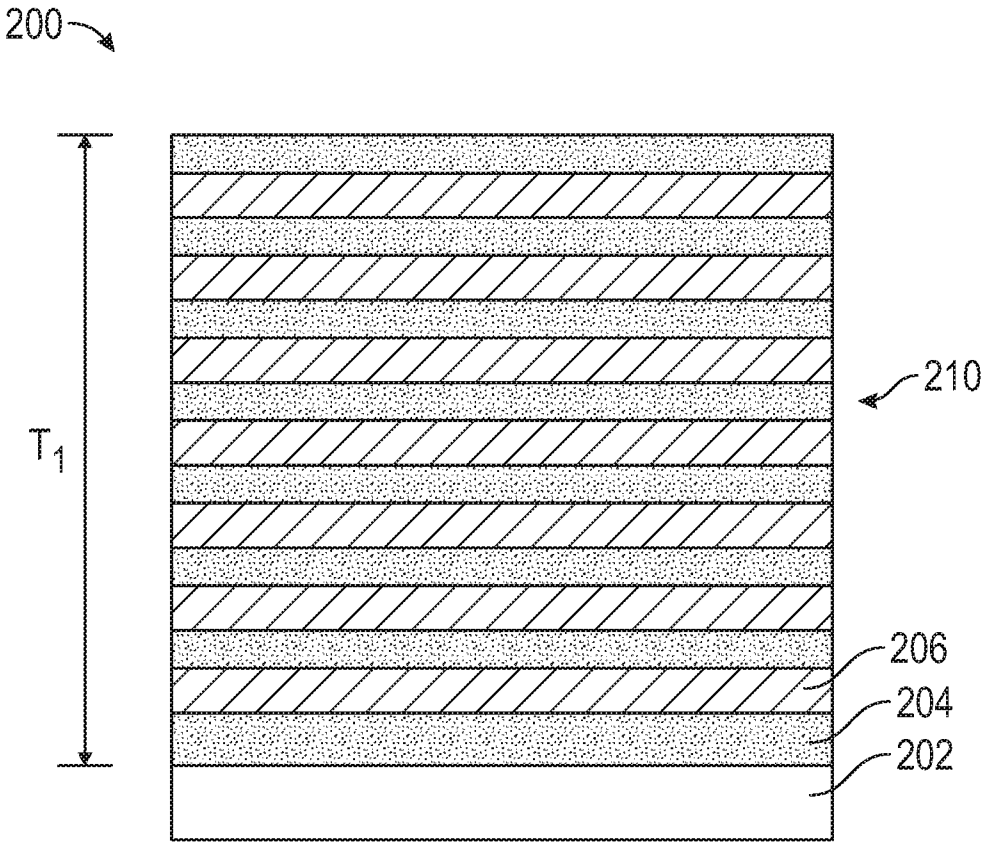


FIG. 2A

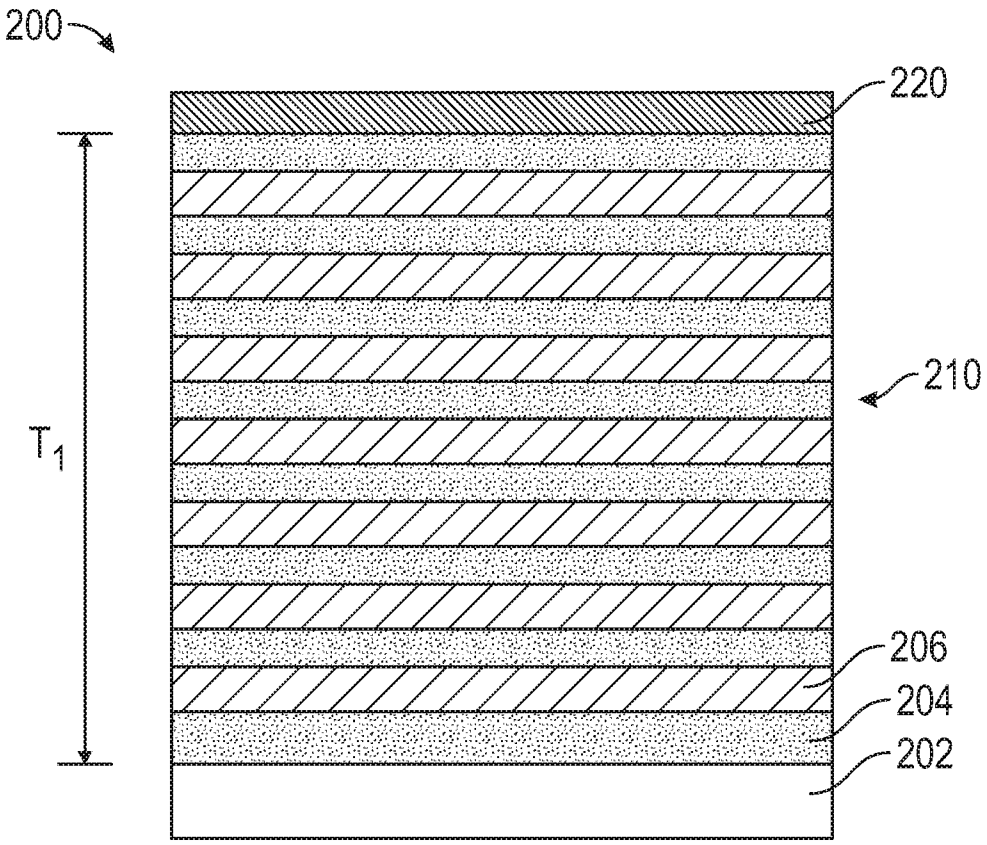


FIG. 2B

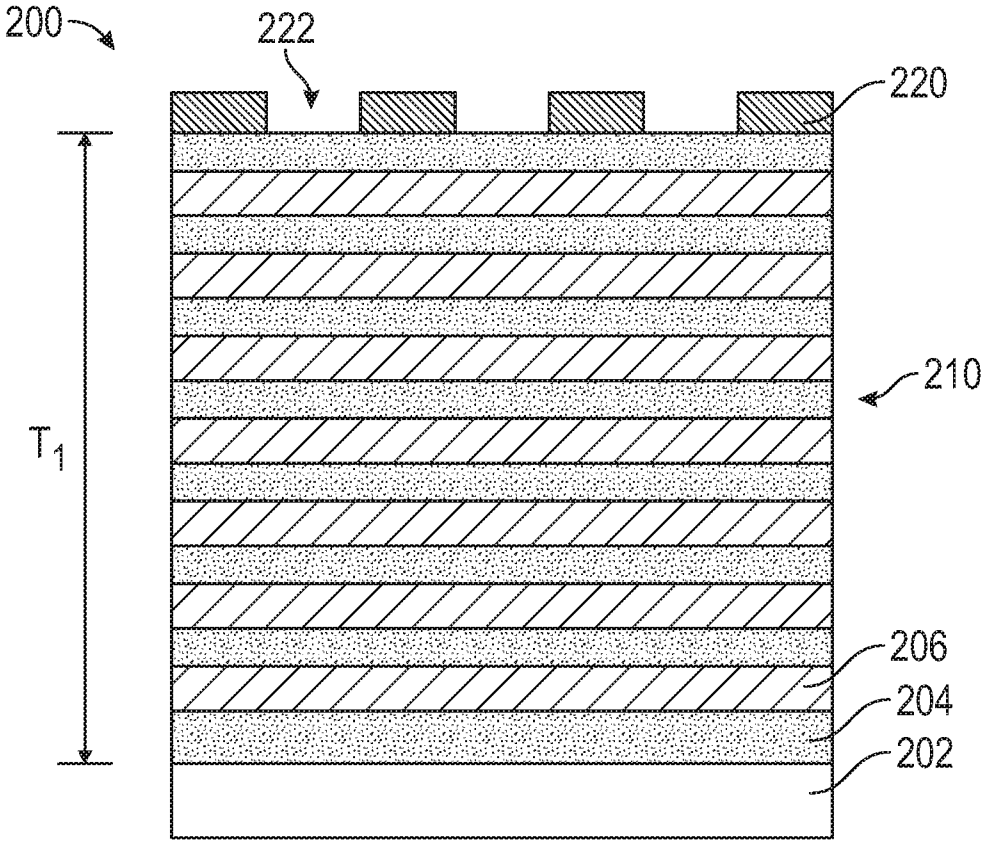

200
222
220
210
T_1
206
204
202

FIG. 2C

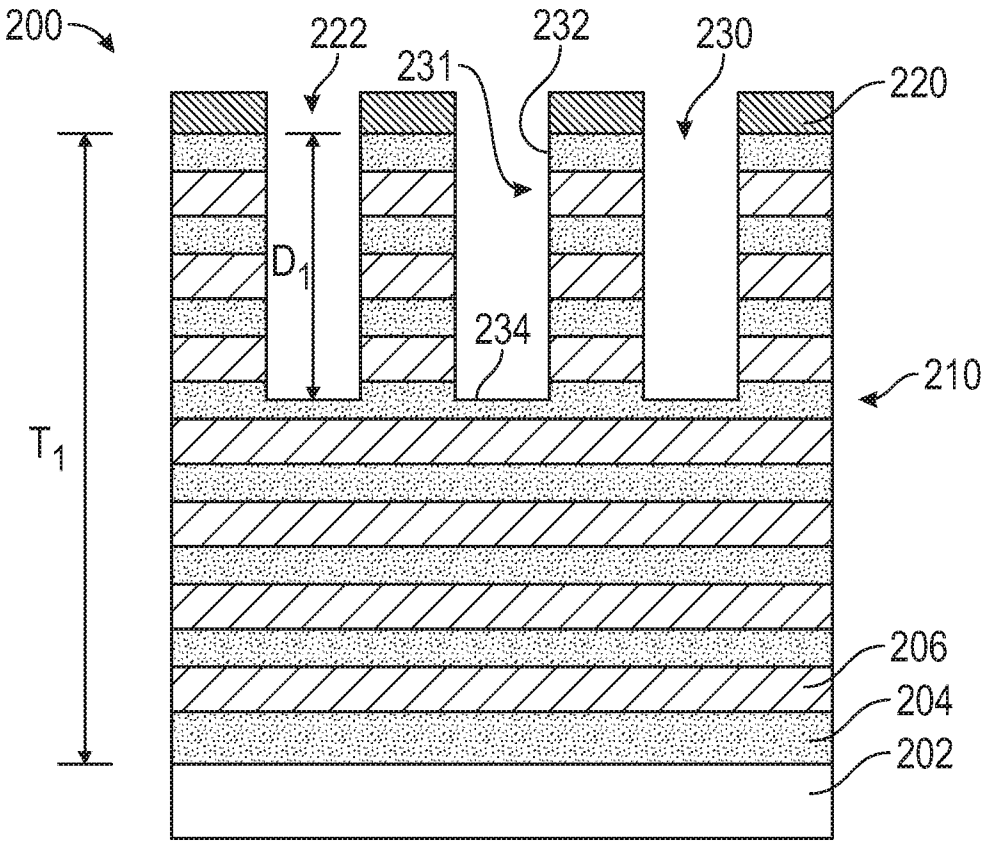

200
222
231
232
230
220
D_1
234
210
T_1
206
204
202

FIG. 2D

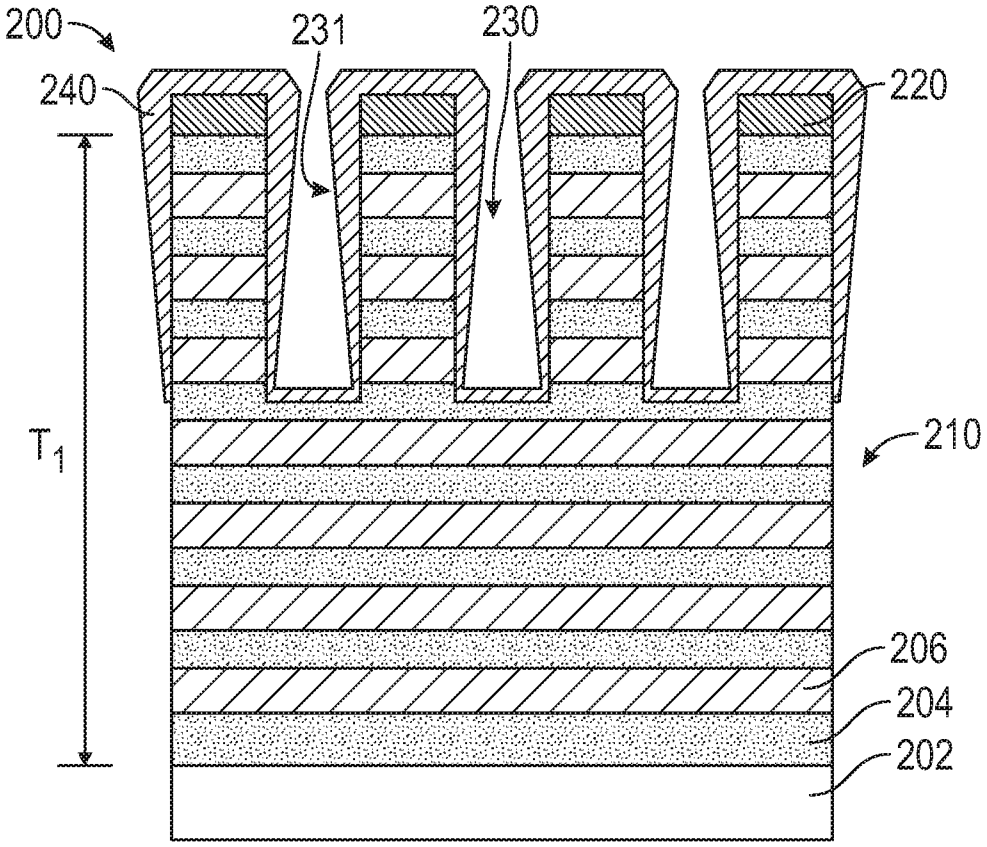

200
231
230
240
220
T_1
210
206
204
202

FIG. 2E

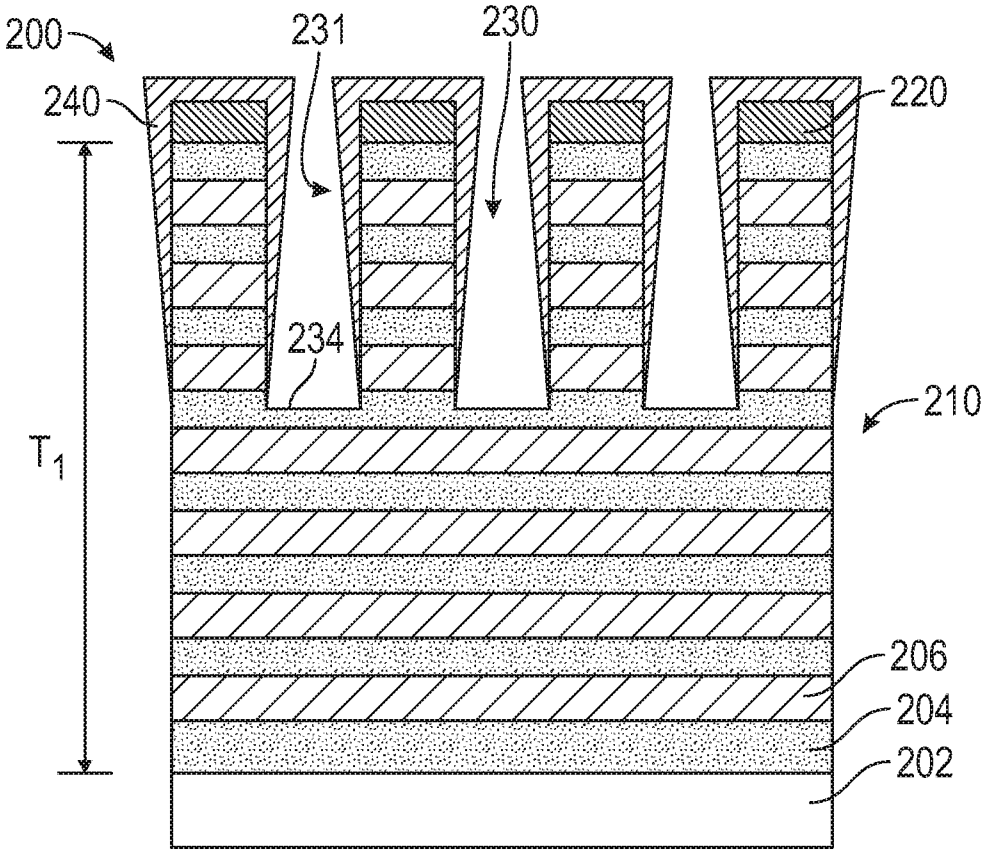

200
231
230
240
220
234
T_1
210
206
204
202

FIG. 2F

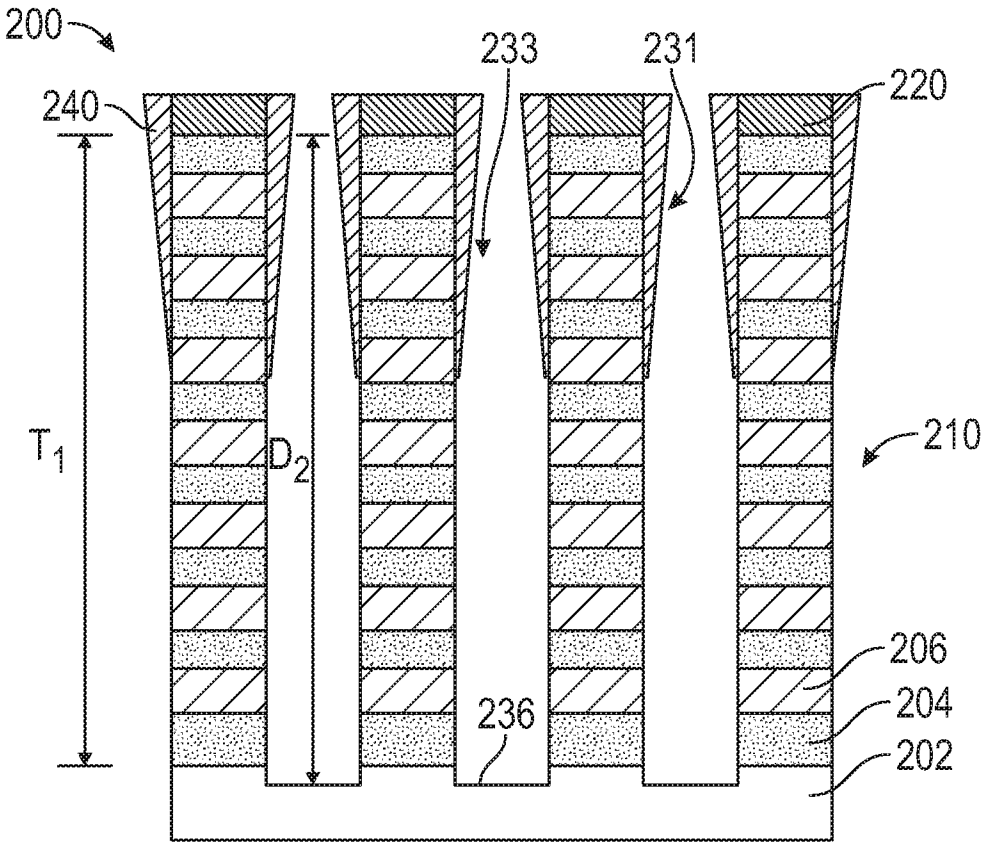

200
233
231
240
220
T_1
D_2
210
206
204
236
202

FIG. 2G

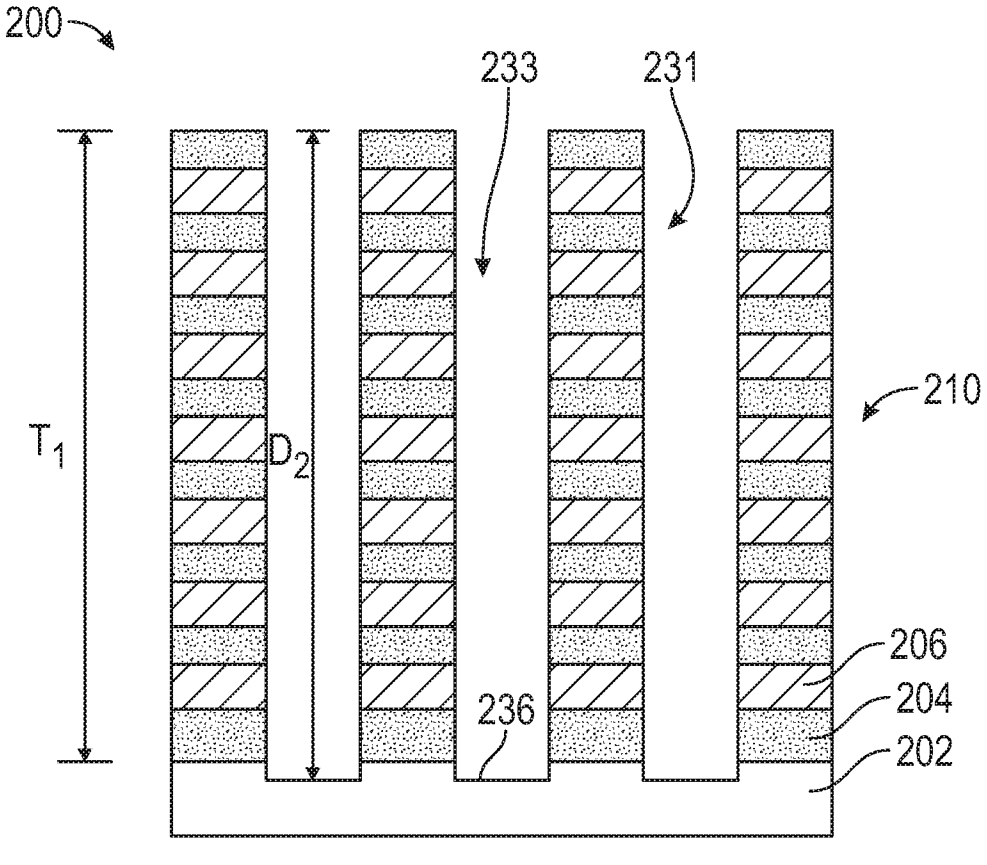

200
233
231
T_1
D_2
210
206
204
236
202

FIG. 2H